r,	Hits	Search Text	DB I	Time stamp
Number				
1	2	("4942554").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 16:46
5	3	6214653.URPN.	USPAT	2003/06/18 16:53
6	12	("5244828" "5258318" "5373803" "5399507" "5493137" "5508219" "5585284" "5830784" "5891763" "5930638" "5956597" "6015745").PN.	USPAT	2003/06/18 16:53
10	2		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:12
16	0	(amorphous) with (ion implant implantation implanting implanted) with periphery with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:13
17	6	(amorphizing amorphization amorphized) with (trench groove recess recessed grooved) with periphery	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:20
18	4	((amorphizing amorphization amorphized) with (trench groove recess recessed grooved) with periphery) not ((amorphizing amorphization amorphized) with periphery with trench and (438/6 257/\$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:14
22	3	(amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ("4676847" "5543348" "5641694" "5843820" "5893735" "5998821" "6093614" "6207493" "6214653" "6238967").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:17
25	45	(amorphizing amorphization amorphized) with (trench groove recess recessed grooved)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:20
55	1017	trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:52
56	1232	trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with mask	USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:56
57	1389	(438/222,226,357,360,363,429,442,for.167,f	obsPAT).CCLS US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	17:53
58	18	(trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with mask) and ((438/222,226,357,360,363,429,442,for.167,	USPAT; US-PGPUB; EPO; JPO; fder@ent;cci IBM_TDB	2003/06/18 17:54 S.)
59	152	trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with mask and (mask with etch adj back etchback)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:56

60	156	trench with (etch etching) and ((oxide	USPAT;	2003/06/18
		dioxide) and nitride) with mask and	US-PGPUB;	17:57
		removing with mask and ((oxid nitrid	EPO; JPO;	
		dioxide mask) with etch adj back	DERWENT;	
		etchback)	IBM_TDB	
61	231		USPAT;	2003/06/18
		dioxide) and nitride) with mask and	US-PGPUB;	17:57
		removing with mask and ((oxide nitrid	EPO; JPO;	
		dioxide mask) with etch adj back	DERWENT;	
	10	etchback)	IBM_TDB USPAT	2003/06/18
62	10	6074954.URPN.	USPAT	18:18
63	15	("4755476" "4895810" "5120668"	USPAT	2003/06/18
63	15	"5160407" "5182234" "5229315"	USPAI	18:19
		"5256583" "5283201" "5318665"		10.15
		"5374584" "5449433" "5453156"		
		"5492850" "5656535" "5731130").PN.		
_	1389	(438/222,226,357,360,363,429,442,for.167,f	אקפאדו ררז.	2003/06/18
-	1309	(430/222,220,337,300,303,429,442,101:107,1	US-PGPUB;	17:53
			EPO; JPO;	1,,00
			DERWENT;	
			IBM TDB	
_	21	(amorphizing amorphization amorphized	USPAT;	2003/06/18
		amorphous) with (ion implant implantation	US-PGPUB;	17:16
		implanting implanted) and	EPO; JPO;	
		((438/222,226,357,360,363,429,442,for.167,		s.)
		((100, 222, 220, 000, 000, 000, 000, 000,	IBM TDB	·
l -	1	(amorphizing amorphization amorphized) and	USPAT;	2003/06/18
		((438/222,226,357,360,363,429,442,for.167,	eus-26Pybcci	SL0:52
ł			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	415	(amorphizing amorphization amorphized)	USPAT;	2003/06/18
	1	and (438/6 257/\$6)	US-PGPUB;	17:11
•			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	342	(amorphizing amorphization amorphized	USPAT;	2003/06/18
		amorphous) with (ion implant implantation	US-PGPUB;	17:21
		implanting implanted) and ((amorphizing	EPO; JPO;	
		amorphization amorphized) and (438/6	DERWENT;	
		257/\$6))	IBM_TDB	2002/06/19
-	45	(amorphizing amorphization amorphized)	USPAT; US-PGPUB;	2003/06/18 17:51
		with (trench groove recess recessed	EPO; JPO;	11:21
		grooved)		
			DERWENT; IBM TDB	
_	227	((amorphizing amorphization amorphized)	USPAT;	2003/06/18
_	221	and (438/6 257/\$6)) and (recrystal	US-PGPUB;	11:32
1		crystal crystallize crystalization	EPO; JPO;	
		crystallizing recrystallize	DERWENT;	
		recrystalization recrystallizing anneal	IBM TDB	
		annealing annealling annealed) with		
		(amorphized amorphous)		
l <u>-</u>	192	((amorphizing amorphization amorphized	USPAT;	2003/06/18
	1,5	amorphous) with (ion implant implantation	US-PGPUB;	11:32
		implanting implanted) and ((amorphizing	EPO; JPO;	
1		amorphization amorphized) and (438/6	DERWENT;	
		257/\$6))) and (((amorphizing	IBM TDB	
		amorphization amorphized) and (438/6	_	
	1	257/\$6)) and (recrystal crystal		
	1	crystallize crystalization crystallizing		
		recrystallize recrystalization		
[recrystallizing anneal annealing	1	
[annealling annealed) with (amorphized	1	
		amorphous))		

_	182	(((amorphizing amorphization amorphized amorphous) with (ion implant implantation	USPAT; US-PGPUB; EPO; JPO;	2003/06/18 11:33
		<pre>implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6))) and (((amorphizing</pre>	DERWENT; IBM TDB	
		amorphization amorphized) and (438/6	12.1_122	
		257/\$6)) and (recrystal crystal crystallizing		
		recrystallize recrystalization		
		recrystallizing anneal annealing annealling annealed) with (amorphized		
	140	amorphous))) not (((amorphizing	USPAT;	2003/06/18
-	140	ámófphózphiønngmemphphedatwonhamorphibed gmosphonetesitheteonedmylentedmplantation	US-PGPUB;	15:42
		վարհերիան արդարան կանութեն լարութեր (amorphizedg amorphozatiwmthmorphized) anddimelancation	EPO; JPO; DERWENT;	
		2mg/antingammplanamdrphmding	IBM TDB	
		4me39M22at20f, amorphn2ed3, 4fd, 4429fer. 167, 257/\$6)) and (recrystal crystal	for.221).CCI	(S.)))
		crystallize crystalization crystallizing		
		recrystallize recrystalization recrystallizing anneal annealing		
		annealling annealed) with (amorphized amorphous))) not (((amorphizing		
		amorphization amorphized) with (trench		
_	0	groove recess recessed grooved)) 65ā前8〒身山東和内g amorphization amorphized	USPAT	2003/06/18
	_	amorphous) with (ion implant implantation	YYG D N M	14:05 2003/06/18
-	10	1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1.	USPAT for.221).CCI	
		änd93654Ming"600m490"med"d2p46558" d6008967Mg.&Mposited) with amorphous		
-	554	trench with DRAm with isolation	USPAT;	2003/06/18
			US-PGPUB; EPO; JPO;	15:45
			DERWENT; IBM TDB	
_	7	(trench with DRAm with isolation) and	USPAT;	2003/06/18
		conformal near (insulator oxide dioxide)	US-PGPUB; EPO; JPO;	15:43
			DERWENT;	
_	4	(trench with DRAm with isolation) and	IBM_TDB USPAT;	2003/06/18
		conformal near (insulator oxide dioxide)	US-PGPUB; EPO; JPO;	15:44
		with trench	DERWENT;	
_	170	trench with DRAm with sti	IBM_TDB USPAT;	2003/06/18
	1,0	Cremen with blank with bol	US-PGPUB;	15:45
			EPO; JPO; DERWENT;	:
		trench with DRAm near2 sti	IBM_TDB USPAT;	2003/06/18
-	8	trench with DRAM hearz sti	US-PGPUB;	15:46
			EPO; JPO; DERWENT;	
			IBM_TDB	2002/06/19
-	53	trench with DRAm near4 sti not (trench with DRAm near2 sti)	USPAT; US-PGPUB;	2003/06/18 15:47
		·	EPO; JPO; DERWENT;	
			IBM_TDB	
-	18	trench with DRAm and conformal near2 (silicon near oxide)	USPAT; US-PGPUB;	2003/06/18 15:48
		(SIIION NOUI SAIMO)	EPO; JPO;	
			DERWENT; IBM TDB	
	L	<u> </u>		· · · · · · · · · · · · · · · · · · ·

,	-	6	trench with DRAm and conformal near2 (silicon near oxide) with trench	USPAT; US-PGPUB; EPO; JPO;	2003/06/18 15:48
				DERWENT; IBM TDB	